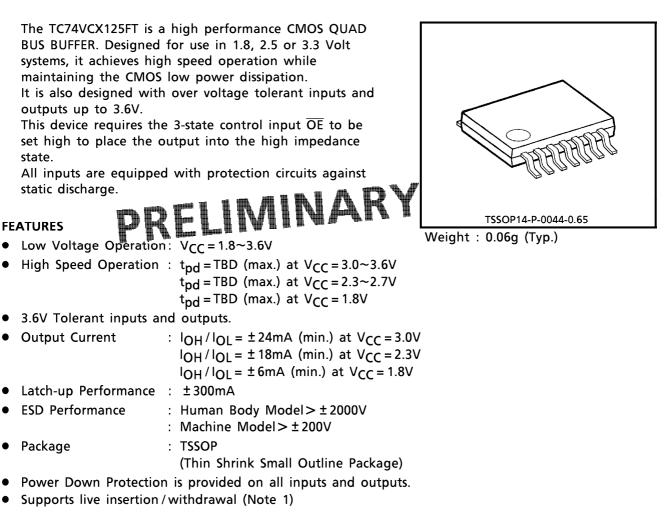
<u>TOSHIBA</u>

ADVANCE TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

T C 7 4 V C X 1 2 5 F T

LOW-VOLTAGE QUAD BUS BUFFER WITH 3.6V TOLERANT INPUTS AND OUTPUTS



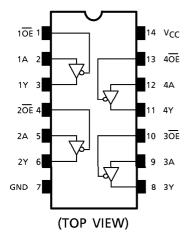
(Note 1) To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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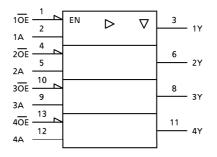
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TOSHIBA

PIN ASSIGNMENT



IEC LOGIC SYMBOL



TRUTH TABLE

INP	UTS	OUTPUTS	DRFIIMINARY
ŌĒ	A	Y	PRELIMINAKY
Н	Х	Z	PKELIWIN
L	L	L	
L	Н	Н	

X : Don't Care

Z : High Impedance

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	Vcc	-0.5~4.6	V
DC Input Voltage	VIN	-0.5~4.6	V
DC Quitput Valtage	Value	-0.5~4.6 (Note 1)	v
DC Output Voltage	Vout	-0.5~V _{CC} +0.5 (Note 2)	v
Input Diode Current	IК	– 50	mA
Output Diode Current	lок	±50 (Note 3)	mA
DC Output Current	ΙΟυτ	± 50	mA
Power Dissipation	PD	180	mW
DC V _{CC} /Ground Current	ICC/IGND	± 100	mA
Storage Temperature	T _{stg}	- 65~150	°C

(Note 1) Off-State

(Note 2) High or Low State. IOUT absolute maximum rating must be observed.

(Note 3) V_{OUT} < GND, V_{OUT} > V_{CC}

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	Maa	1.8~3.6	v
Supply Voltage	Vcc	1.2~3.6 (Note 4)	
Input Voltage	VIN	-0.3~3.6	V
Output Voltage	Maria	0~3.6 (Note 5)	v
Output voltage	Vout	0~ V _{CC} (Note 6)	
		±24 (Note 7)	
Output Current	IOH / IOL	± 18 (Note 8)	mA
		±6 (Note 9)	
Operating Temperature	T _{opr}	- 40~85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 10)	ns / V

(Note 4) Data Retention Only

- (Note 5) Off-State
- (Note 7) $V_{CC} = 3.0 \sim 3.6V$ **PRELIMINARY** (Note 8) $V_{CC} = 2.3 \sim 2.7V$

- (Note 9) V_{CC} = 1.8V
- (Note 10) $V_{IN} = 0.8 \sim 2.0 V$, $V_{CC} = 3.0 V$

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = $-40 \sim 85^{\circ}$ C, 2.7V < V_{CC} \leq 3.6V)

PARAMETER		SYMBOL	TEST CON	DITION	V _{CC} (V)	MIN.	MAX.	UNIT
Input	"H" Level	VIH			2.7~3.6	2.0		v
Voltage	"L" Level	VIL			2.7~3.6		0.8	V
				I _{OH} = – 100μA	2.7~3.6	V _{CC} - 0.2		
	"H" Level	∨он	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -12mA$	2.7	2.2	_	
0				I _{OH} = – 18mA	3.0	2.4	_	
Output				$I_{OH} = -24mA$	3.0	2.2		V
Voltage		V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	l _{OL} = 100μA	2.7~3.6	_	0.2	
	"L" Level			I _{OL} = 12mA	2.7	_	0.4	
				I _{OL} = 18mA	3.0	_	0.4	
				$I_{OL} = 24mA$	3.0	_	0.55	
Input Leaka	age Current	^I IN	V _{IN} = 0~3.6V	•	2.7~3.6	_	± 5.0	μA
3-State Out Off-State C	•	loz	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6V$		2.7~3.6	_	± 10.0	μΑ
Power Off Leakage Current		lOFF	V _{IN} , V _{OUT} = 0~3.6V		0	_	10.0	μΑ
Quiescent Supply			$V_{IN} = V_{CC}$ or GND		2.7~3.6	_	20.0	•
Current			2.7~3.6	_	±20.0	μΑ		
Increase In Input	ICC Per	∆ا∠C	V _{IH} = V _{CC} – 0.6V		2.7~3.6		750	μΑ

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = $-40 \sim 85^{\circ}$ C, $2.3V \leq V_{CC} \leq 2.7V$)

PARAMETER		SYMBOL	TEST CONDITION		V _{CC} (V)	MIN.	MAX.	UNIT
Input	"H" Level	VIH			2.3~2.7	1.6		v
Voltage	"L" Level	VIL			2.3~2.7	_	0.7	
				I _{OH} = – 100μA	2.3~2.7	V _{CC} - 0.2	_	
	"H" Level	Vон	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -6mA$	2.3	2.0	_	V
Output Voltage				$I_{OH} = -12mA$	2.3	1.8	_	
				I _{OH} = – 18mA	2.3	1.7	_	
		V _{OL}	V _{IN} =V _{IH} or V _{IL}	l _{OL} = 100μA	2.3~2.7	_	0.2	
	"L" Level			I _{OL} = 12mA	2.3	_	0.4	
				I _{OL} = 18mA	2.3	_	0.6	
Input Leakag	ge Current	IN	V _{IN} = 0~3.6V		2.3~2.7	_	± 5.0	μΑ
3-State Output Off-State Current		loz	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6V$		2.3~2.7	_	± 10.0	μΑ
Power Off Leakage Current		IOFF	V _{IN} , V _{OUT} = 0~3.6V		0	_	10.0	μA
Quiescent Supply			V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0	
Current		lcc	V _{CC} ≦ (V _{IN} , V _{OUT})≦ 3.6V _{CC}		2.3~2.7	-2.7 <u> </u>	±20.0	μΑ

PRELIMINARY

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = $-40 \sim 85^{\circ}$ C, $1.8V \le V_{CC} < 2.3V$)

PARAI	METER	SYMBOL	TEST CONDITION		V _{CC} (V)	MIN.	MAX.	UNIT
Input	"H" Level	VIH			1.8~2.3	0.7 x V _{CC}	_	v
Voltage "L" Leve		VIL			1.8~2.3	_	0.2 x V _{CC}	v
	"H" Level		V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100μA	1.8	V _{CC} - 0.2	_	
Output		Voн		$I_{OH} = -6mA$	1.8	1.4	_	V
Voltage	"L" Level	V _{OL}	$V_N = V_{IH}$ or V_{IL}	l _{OL} = 100μA	1.8	—	0.2	
				I _{OL} = 6mA	1.8		0.3	
Input Leaka	Input Leakage Current		V _{IN} = 0~3.6V		1.8	—	± 5.0	μA
3-State Output Off-State Current		loz	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6V$		1.8	-	± 10.0	μΑ
Power Off Leakage Current		lOFF	V _{IN} , V _{OUT} = 0~3.6V		0	_	10.0	μΑ
Quiescent S	Quiescent Supply		$V_{IN} = V_{CC}$ or GND		1.8	_	20.0	
Current		lcc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6V$		1.8		±20.0	μΑ

AC characteristics (Ta = $-40 \sim 85^{\circ}$ C, Input t_r = t_f = 2.0ns, C_L = 30pF, R_L = 500 Ω)

PARAMETER	SYMBOL	TRANSPORT	V _{CC} (V)	MIN.	MAX.	UNIT
Propagation Dolay			1.8	1.5	TBD	
Propagation Delay Time	∰L ∪pL # ••• •••	(Fig.1, 2)	2.5 ± 0.2	1.0	TBD	ns
line	^t pHL		3.3±0.3	0.8	TBD	
2 State Output Enable	+		1.8	1.5	TBD	
3-State Output Enable Time	t _{pZL}	(Fig.1, 3)	2.5 ± 0.2	1.0	TBD	ns
Time	^t pZH		3.3±0.3	0.8	TBD	
2 State Output Disable	+		1.8	1.5	TBD	
3-State Output Disable Time	t _{pLZ}	(Fig.1, 3)	2.5 ± 0.2	1.0	TBD	ns
	^t pHZ		3.3 ± 0.3	0.8	TBD	
Output To Output	+		1.8	_	TBD	
Output To Output Skew	tosLH	(Note 11)	2.5 ± 0.2	_	TBD	ns
JNEW	^t osHL		3.3±0.3	_	TBD	

For $C_L = 50pF$, add approximately 300ps to the AC maximum specification.

(Note 11) Parameter guaranteed by design. $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$

PARAMETER	SYMBOL	TEST CONDITI	ON	V _{CC} (V)	TYP.	UNIT
		V _{IH} = 1.8V, V _{IL} = 0V	(Note 12)	1.8	TBD	
Quiet Output Maximum	VOLP	$V_{IH} = 2.5V, V_{IL} = 0V$	(Note 12)	2.5	TBD	v
Dynamic V _{OL}		V _{IH} = 3.3V, V _{IL} = 0V	(Note 12)	3.3	TBD	
Quiat Qutaut Minimum	VOLV	V _{IH} = 1.8V, V _{IL} = 0V	(Note 12)	1.8	TBD	
Quiet Output Minimum Dynamic V _{OL}		$V_{IH} = 2.5V, V_{IL} = 0V$	(Note 12)	2.5	TBD	V
		V _{IH} = 3.3V, V _{IL} = 0V	(Note 12)	3.3	TBD	
Quiet Qutput Minimum	Vohv	$V_{IH} = 1.8V, V_{IL} = 0V$	(Note 12)	1.8	TBD	
Quiet Output Minimum Dynamic V _{OH}		$V_{IH} = 2.5V, V_{IL} = 0V$	(Note 12)	2.5	TBD	V
		V _{IH} = 3.3V, V _{IL} = 0V	(Note 12)	3.3	TBD	

Dynamic switching characteristics (Ta = 25° C, Input t_r = t_f = 2.0ns, C_L = 30pF)

(Note 12) Parameter guaranteed by design.

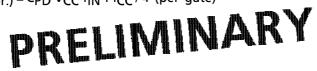
Capacitive characteristics $(Ta = 25^{\circ}C)$

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	TYP.	UNIT
Input Capacitance	C _{IN}		1.8, 2.5, 3.3	TBD	рF
Output Capacitance	COUT		1.8, 2.5, 3.3	TBD	pF
Power Dissipation Capacitance	C _{PD}	f _{IN} = 10MHz (Note 13)	1.8, 2.5, 3.3	TBD	pF

(Note 13) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

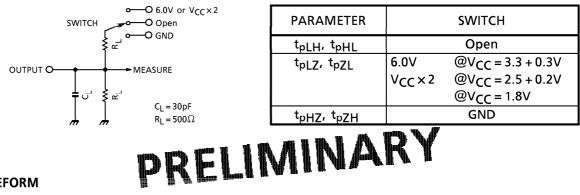
Average operating current can be obtained by the equation :

 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 4$ (per gate)



TOSHIBA

Fig.1 Test Circuit



AC WAVEFORM

Fig.2 t_{pLH}, t_{pHL}

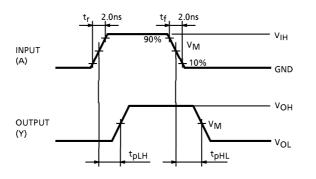
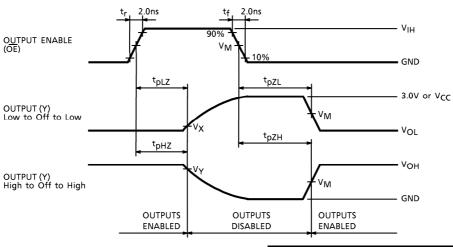
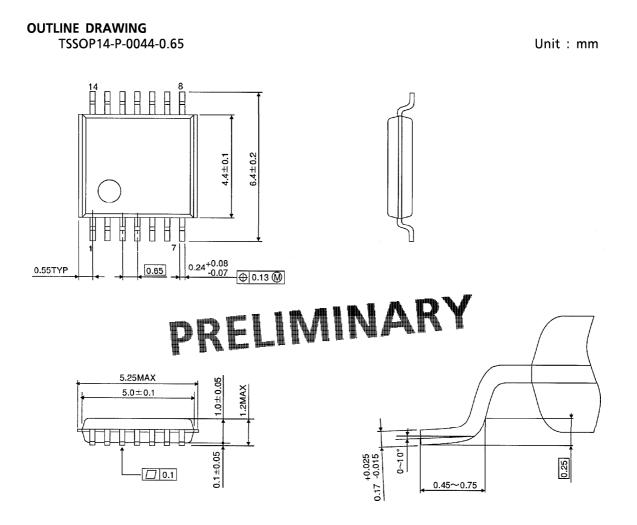


Fig.3 t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}



SYMBOL	V _{CC}						
3 TIVIBOL	3.3±0.3V	2.5±0.2V	1.8V				
VIH	2.7V	Vcc	V _{CC}				
٧ _M	1.5V	V _{CC} /2	V _{CC} /2				
٧ _X	V _{OL} + 0.3V	V _{OL} + 0.15V	V _{OL} + 0.15V				
٧ _Y	V _{OH} – 0.3V	V _{OH} – 0.15V	V _{OH} – 0.15V				

1998-09-01 7/8



Weight : 0.06g (Typ.)

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